Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

DUAL 40V PNP SURFACE MOUNT TRANSISTOR

Features

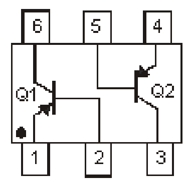
- V_{CEO} = -40V
- I_C = -200mA
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- **Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)**
- **“Green” Device (Note 2)**
- **Ultra Small Package**

Mechanical Data

- Case: SOT-963
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0027 grams (approximate)

SOT-963

Top View



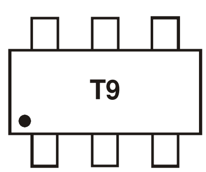
Device Schematic

Ordering Information

Device	Packaging	Shipping
DST3906DJ-7	SOT-963	10,000/Tape & Reel

Notes: 1. No purposefully added lead. Halogen and Antimony Free.
2. Diodes Inc’s “Green” Policy can be found on our website at http://www.diodes.com

Marking Information



T9 = Product Type Marking Code

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous (Note 3)	I_C	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 3)	$R_{\theta JA}$	417	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes: 3. Device mounted on FR-4 PCB with minimum recommended pad layout.

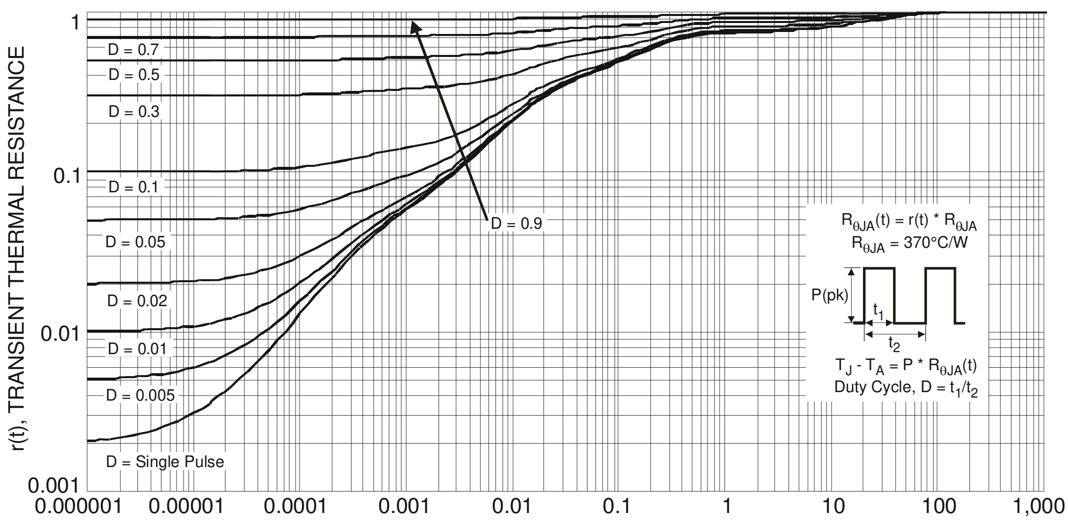


Fig. 1 Transient Thermal Response

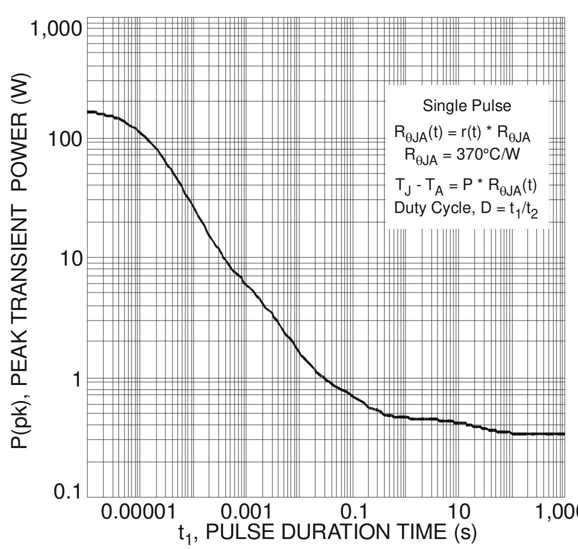


Fig. 2 Single Pulse Maximum Power Dissipation

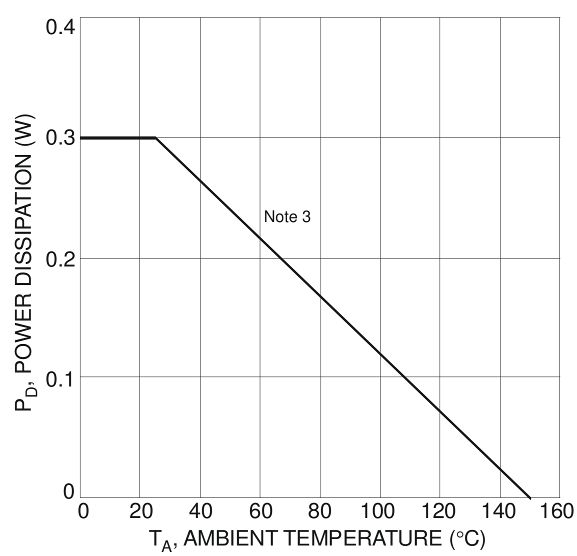


Fig. 3 Power Dissipation vs. Ambient Temperature

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	—	V	I_C = -10µA, I_E = 0
Collector-Emitter Breakdown Voltage (Note 4)	$V_{(BR)CEO}$	-40	—	V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0	—	V	I_E = -10µA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3.0V
	I_{CBO}	—	-50	nA	V_{CB} = -30V, I_E = 0
Base Cutoff Current	I_{BL}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3.0V
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h_{FE}	60 80 100 60 30	— — 300 — —	—	I_C = -100µA, V_{CE} = -1.0V I_C = -1.0mA, V_{CE} = -1.0V I_C = -10mA, V_{CE} = -1.0V I_C = -50mA, V_{CE} = -1.0V I_C = -100mA, V_{CE} = -1.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.25 -0.40	V	I_C = -10mA, I_B = -1.0mA I_C = -50mA, I_B = -5.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.65 —	-0.85 -0.95	V	I_C = -10mA, I_B = -1.0mA I_C = -50mA, I_B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.5	pF	V_{CB} = -5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	10	pF	V_{EB} = -0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	2.0	12	kΩ	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	10	x 10^{-4}	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	3.0	60	µS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = -20V, I_C = -10mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	V_{CC} = -3.0V, I_C = -10mA,
Rise Time	t_r	—	35	ns	$V_{BE(off)}$ = 0.5V, I_{B1} = -1.0mA
Storage Time	t_s	—	225	ns	V_{CC} = -3.0V, I_C = -10mA,
Fall Time	t_f	—	75	ns	I_{B1} = I_{B2} = -1.0mA

Notes: 4. Short duration pulse test used to minimize self-heating effect.

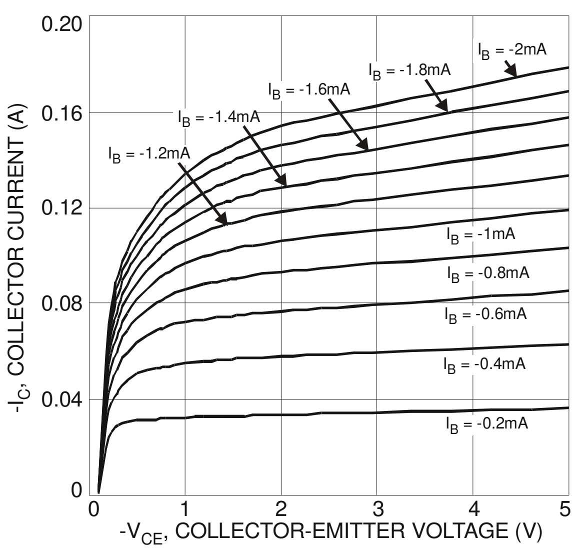


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

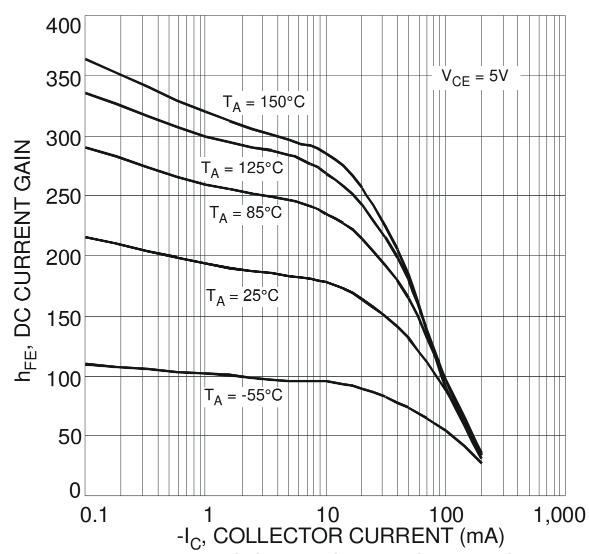


Fig. 5 Typical DC Current Gain vs. Collector Current

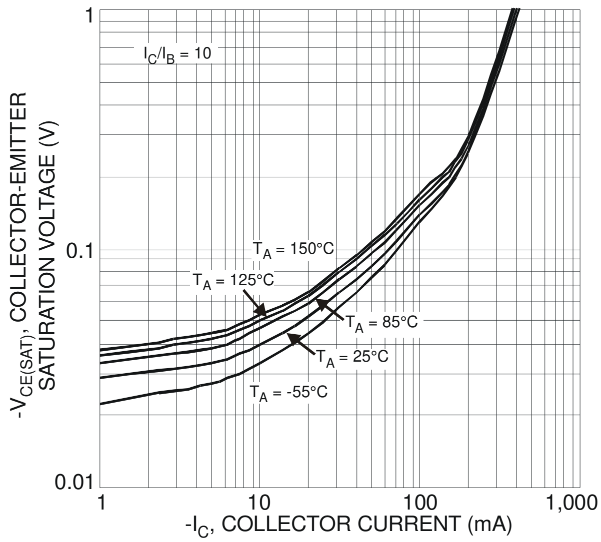


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

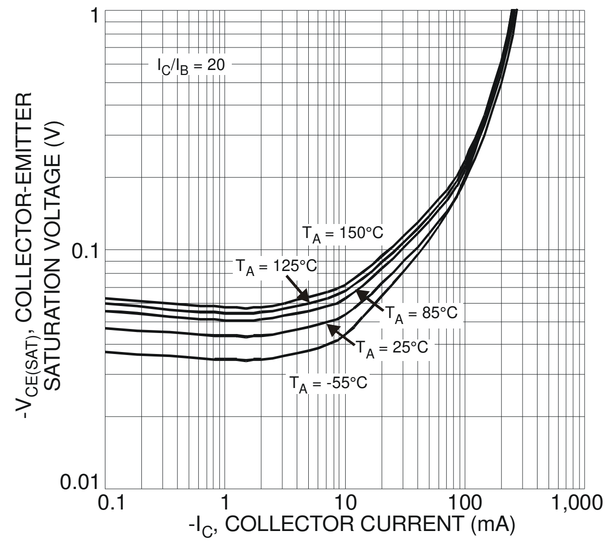


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

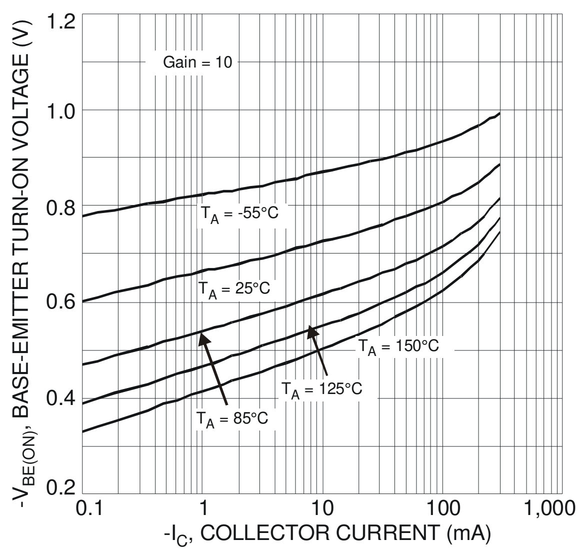


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

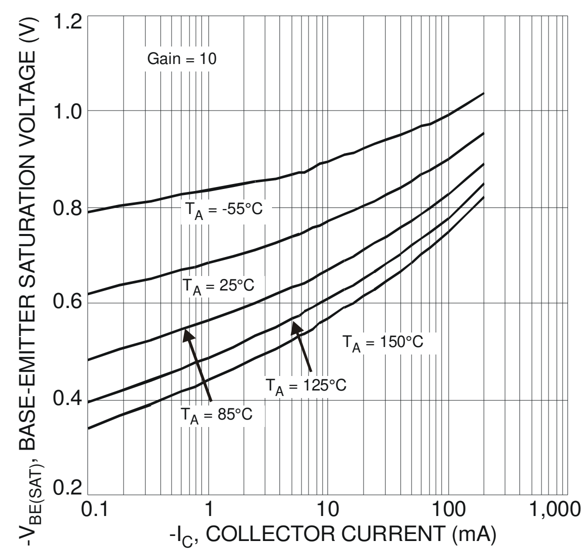


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

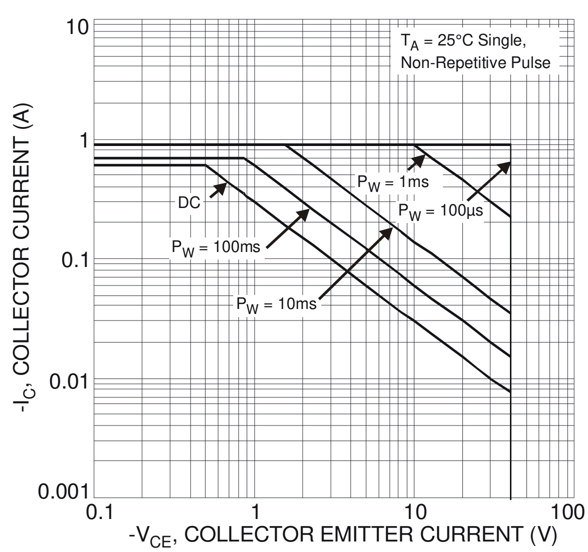
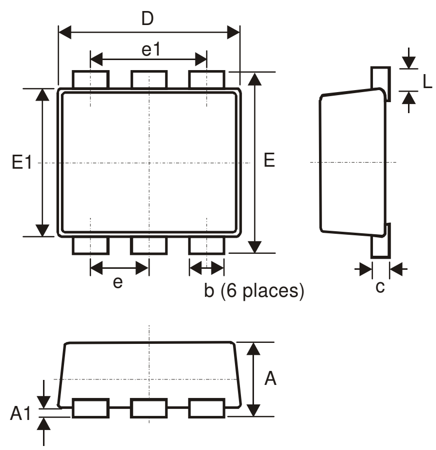


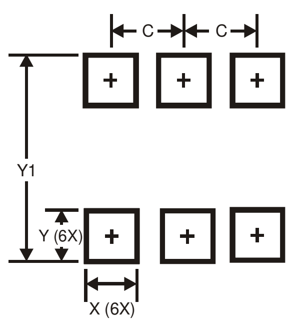
Fig. 10 Safe Operation Area (PNP)

Package Outline Dimensions



SOT-963			
Dim	**Min**	**Max**	**Typ**
A	0.40	0.50	0.45
A1	0	0.05	-
C	0.120	0.180	0.150
D	0.95	1.05	1.00
E	0.95	1.05	1.00
E1	0.75	0.85	0.80
L	0.05	0.15	0.10
b	0.10	0.20	0.15
e	0.35 Typ		
e1	0.70 Typ		
All Dimensions in mm			

Suggest Pad Layout



Dimensions	Value (in mm)
C	0.350
X	0.200
Y	0.200
Y1	1.100

IMPORTANT NOTICE

LIFE SUPPORT

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